

# Claims

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[c1]

A method for forming an interconnect structure in a magnetic random access memory (MRAM) device, the method comprising:

defining a magnetic stack layer on a lower metallization level, said magnetic stack layer including a non-ferromagnetic layer disposed between a pair of ferromagnetic layers;

defining a conductive hardmask over said magnetic stack layer; and

removing selected portions of said hardmask and said magnetic stack layer, thereby creating an array of magnetic tunnel junction (MTJ) stacks, said MTJ stacks including remaining portions of said magnetic stack layer and said hardmask;

wherein said hardmask forms a self aligning contact between said magnetic stack layer and an upper metallization level subsequently formed above said MTJ stacks.

wherein  
in MTJ

[c2]

The method of claim 1, further comprising:

depositing a cap layer over said MTJ stacks and exposed portions of said lower metallization level;

depositing an interlevel dielectric (ILD) layer over said

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cap layer; and  
defining openings for said upper metallization level in  
said ILD layer;  
wherein portions of said cap layer atop said MTJ stacks  
are used as an etch stop.

[c3] The method of claim 2, further comprising:  
defining via openings in said ILD layer, wherein portions  
of said cap layer atop said lower metallization level are  
used as an etch stop.

[c4] The method of claim 3, further comprising:  
removing portions of said cap layer exposed by said up-  
per metallization openings and said via openings; and  
filling said upper metallization openings and said via  
openings with a conductive material by dual damascene  
processing.

[c5] The method of claim 1, wherein said hardmask com-  
prises a conductive material selected from the group of:  
tantalum, tungsten, titanium, tantalum nitride, tungsten  
nitride, titanium nitride, and combinations comprising at  
least one of the foregoing.

[c6] The method of claim 2, wherein said cap layer comprises  
silicon nitride.

[c7] The method of claim 1, further comprising:

depositing a cap layer over said MTJ stacks and exposed portions of said lower metallization level;  
depositing an interlevel dielectric (ILD) layer over said cap layer; and  
defining via openings in said ILD layer, wherein portions of said cap layer atop said lower metallization level are used as an etch stop.

[c8] The method of claim 8, further comprising:  
subsequent to defining said via openings, defining openings for said upper metallization level in said ILD layer;

wherein portions of said cap layer atop said MTJ stacks are used as an etch stop.

[c9] The method of claim 9, further comprising:  
removing portions of said cap layer exposed by said upper metallization openings and said via openings; and  
filling said upper metallization openings and said via openings with a conductive material by dual damascene processing.

[c10] A magnetic random access memory (MRAM) device, comprising:  
a magnetic stack layer formed on a lower metallization level, said magnetic stack layer including a non-ferromagnetic layer disposed between a pair of ferro-

magnetic layers;  
a conductive hardmask layer formed over said magnetic stack layer; and  
an array of magnetic tunnel junction (MTJ) stacks, said MTJ stacks created by the removal of selected portions of said hardmask layer and said magnetic stack layer, wherein said MTJ stacks including remaining portions of said magnetic stack layer and said hardmask layer, and wherein said hardmask layer forms a self aligning contact between said magnetic stack layer and an upper metallization level formed above said MTJ stacks.

[c11] The MRAM device of claim 11, further comprising:  
a cap layer deposited over the MTJ stacks and exposed portions of the lower metallization level;  
an interlevel dielectric (ILD) layer deposited over said cap layer; and  
a plurality of upper metallization level openings formed in said ILD layer;  
wherein portions of said cap layer atop said MTJ stacks are used as an etch stop for said upper metallization openings.

[c12] The MRAM device of claim 12, further comprising:  
a plurality of via openings defined in said ILD layer, wherein portions of said cap layer atop said lower metallization level are used as an etch stop for said via open-

ings.

[c13] The MRAM device of claim 13, further comprising:  
a conductive material filled into said upper metallization  
openings and said via openings, wherein said conductive  
material contacts lower metallization level and said  
hardmask layer after removal of portions of said cap  
layer.

[c14] The MRAM device of claim 11, wherein said hardmask  
layer comprises a conductive material selected from the  
group of: tantalum, tungsten, titanium, tantalum nitride,  
tungsten nitride, titanium nitride, and combinations  
comprising at least one of the foregoing.

[c15] The MRAM device of claim 12, wherein said cap layer  
comprises silicon nitride.